**Product data sheet** 

## 1. General description

EEPP<sup>™</sup>- Efficiency Enhanced Pt Planar rectifier in a SOD59 (2-lead TO-220AC) plastic package.

### 2. Features and benefits

- Fast switching
- · Reduces switching losses with improved lower reverse recovery charge
- · Soft recovery characteristics
- Low thermal resistance
- · Low leakage current
- Planar termination structure
- High operating temperature capability (T<sub>i (max)</sub> = 175°C)
- Higher I<sub>FSM</sub> capability

## 3. Applications

- · Switched-Mode Power Supplies
- Power factor correction diode
- Uninterrupted Power Supply

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit	
Absolute	maximum rating						
$V_{RRM}$	repetitive peak reverse voltage		1200				V
$I_{F(AV)}$	average forward current	$\delta$ = 0.5 ; square-wave pulse; $T_{mb} \le$ 123 °C; Fig. 1; Fig. 2; Fig. 3	8			А	
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; $t_p$ = 25 $\mu$ s; $T_{mb} \le$ 123 °C; square-wave pulse	16		А		
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	100		А		
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse;	110		Α		
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 8 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>		-	2.4	3.2	V
		I <sub>F</sub> = 8 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>		-	2.0	-	V
Dynamic	characteristics	'					
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_i = 25 \text{ °C}; Fig. 7$		-	-	55	ns
						· ·	

# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	K — A
2	А	anode	}	001aaa020
mb	mb	mounting base; connected to cathod	1 2 TO-220AC (SOD59)	

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package	ackage				
	Name	Description	Version			
BYC8-1200P		Plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59			

# 7. Marking

#### Table 4. Marking codes

Type number	Marking codes
BYC8-1200P	BYC8-1200P

# 8. Limiting values

#### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
$V_{RRM}$	repetitive peak reverse voltage		1200	V
$V_{RWM}$	crest working reverse voltage		1200	V
$V_R$	reverse voltage	DC	1200	V
$I_{F(AV)}$	average forward current	$\delta$ = 0.5 ; square-wave pulse; T <sub>mb</sub> ≤ 123 °C; Fig. 1; Fig. 2; Fig. 3	8	А
I <sub>FRM</sub>	repetitive peak forward current	$δ = 0.5$ ; $t_p = 25 \mu s$ ; $T_{mb} \le 123 °C$ ; square-wave pulse	16	А
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	100	А
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse;	110	А
T <sub>stg</sub>	storage temperature		-65 to 175	°C
T <sub>j</sub>	junction temperature		175	°C

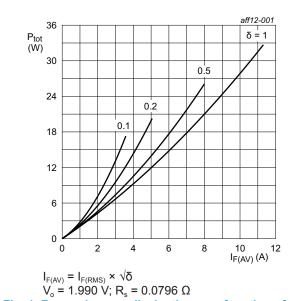
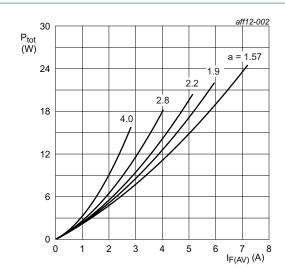


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

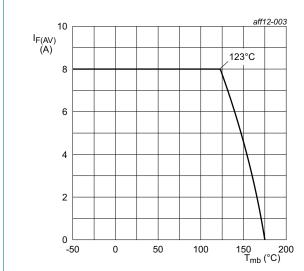


a = form factor =  $I_{F(RMS)}/I_{F(AV)}$ Vo = 1.990 V; Rs = 0.0796  $\Omega$ 

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

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Hyperfast power diode





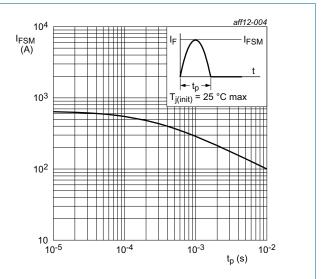
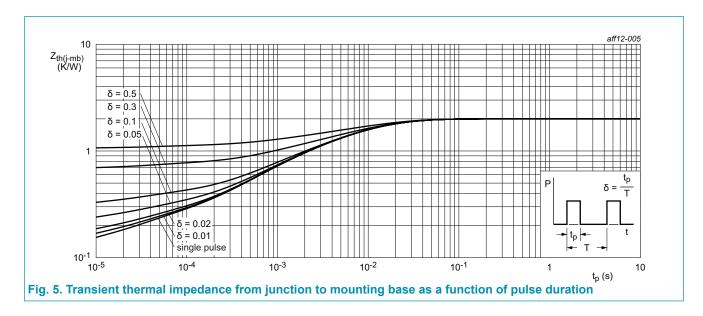


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

## 9. Thermal characteristics

### **Table 6. Thermal characteristics**

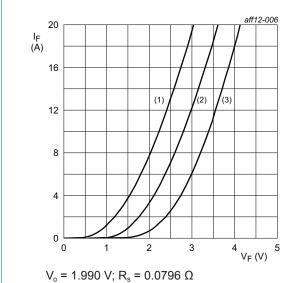
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance from junction to mounting base	Fig. 5	-	-	2	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W



## 10. Characteristics

**Table 7. Characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics					
V <sub>F</sub>	forward current	I <sub>F</sub> = 8 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>	-	2.4	3.2	V
		I <sub>F</sub> = 8 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>	-	2.0	-	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 1200 V; T <sub>j</sub> = 25 °C	-	-	100	μΑ
		V <sub>R</sub> = 1200 V; T <sub>j</sub> = 150 °C	-	-	0.5	mA
Dynamic	characteristics				'	
Q <sub>r</sub>	reverse charge	$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	215	-	nC
		$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	475	-	nC
		$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 150 \text{ °C}; Fig. 7$	-	525	-	nC
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	55	ns
		$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	46	-	ns
		$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	85	-	ns
		$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 150 \text{ °C}; Fig. 7$	-	90	-	ns
I <sub>RM</sub>	peak reverse recovery current	$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	9.2	-	А
		$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	11.2	-	А
		$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_i = 150 \text{ °C}; Fig. 7$	-	12	-	А





<sup>(1)</sup>  $T_j = 150$  °C; typical values (2)  $T_j = 150$  °C; maximum values

<sup>(3)</sup>  $T_i = 25$  °C; maximum values Fig. 6. Forward current as a function of forward voltage

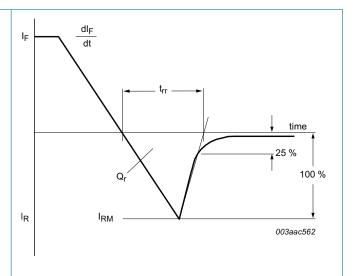


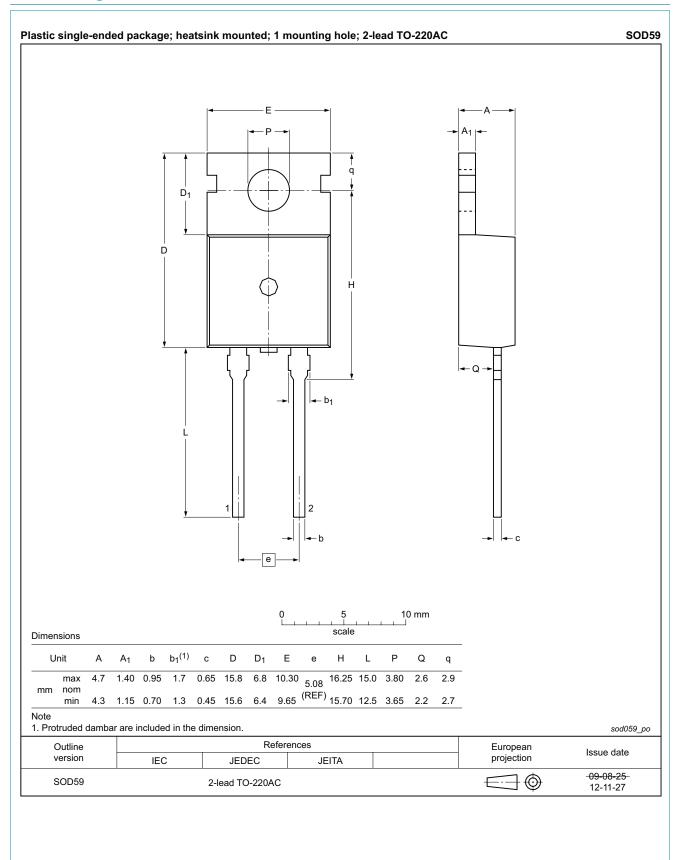
Fig. 7. Reverse recovery definitions; ramp recovery

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# 11. Package outline



**Product data sheet** 

## 12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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